

**WHAT IS CLAIMED IS:**

1. A capacitor device, comprising:
  - a first electrode located over a substrate and connected to a first interconnect;
  - a first insulating layer located over the first electrode;
  - a second electrode located over the first insulating layer and connected to a second interconnect;
  - a second insulating layer located over the second electrode; and
  - a third electrode located over the second insulating layer and connected to the first interconnect.
2. The capacitor device recited in Claim 1 wherein the third electrode is located over the first and second electrodes.
3. The capacitor device recited in Claim 1 further comprising a third insulating layer located over the third electrode, wherein the first and second interconnects are located over the third insulating layer.
4. The capacitor device recited in Claim 1 wherein:
  - the first electrode and the first interconnect are connected by a first via;
  - the second electrode and the second interconnect are connected by a second via; and
  - the third electrode and the first interconnect are connected by a third via.

5. The capacitor device recited in Claim 4 wherein at least one of the first, second and third vias and at least one of the first and second interconnects are collectively a dual-damascene structure.
6. The capacitor device recited in Claim 1 wherein the first insulating layer includes an insulation layer and an etch stop layer located over the insulation layer.
7. The capacitor device recited in Claim 1 wherein a first perimeter of the first electrode envelopes a second perimeter of the second electrode.
8. The capacitor device recited in Claim 7 wherein the second perimeter envelopes a third perimeter of the third electrode.
9. The capacitor device recited in Claim 1 wherein the first electrode comprises copper.
10. The capacitor device recited in Claim 1 wherein the second and third electrodes each comprise a same one selected from the group consisting of:
  - tungsten;
  - tungsten silicide;
  - aluminum;
  - titanium; and
  - titanium nitride.

16. The method recited in Claim 15 wherein the first interconnect is a dual-damascene structure having:
- a trench portion over the third insulating layer; and
  - a via portion extending through at least the first and third insulating layers.
17. The method recited in Claim 15 wherein forming the first insulating layer includes forming an insulation layer and forming an etch stop layer over the insulation layer.
18. The method recited in Claim 14 wherein at least one of the first, second and third electrodes comprises a plurality of conductive layers.
19. A semiconductor device, comprising:
- a transistor element located over a substrate and having a contact;
  - a capacitor element, including:
    - a first electrode located over the substrate;
    - a first insulating layer located over the first electrode;
    - a second electrode located over the first insulating layer;
    - a second insulating layer located over the second electrode; and
    - a third electrode located over the second insulating layer;
  - a dielectric layer located over the transistor element and the capacitor element;
  - a first interconnect located over the dielectric layer, coupled to the first electrode by a first via, and coupled to the third electrode by a second via; and